



Bipolar PNP Bare Die – BTP6088

Part Description

The BTP6088 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6080

Key Parameters:

- VCBO = -50V
- VCEO = -50V
- VEBO = -8V
- hFE = 68-330 @ VCE = -3V, IC = -0.01A
- VCE(Sat) = -0.55V @ IC = -0.15A, IB = -15mA
- fT = 230 MHz @ VCE = -5V, IE = 0A
- COBO = 12pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to RENESAS 2SA673A or ROHM 2SA854S

Die Size (Unawn)

450 μ m X 450 μ m, 18 Mils X 18 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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